

# FDMC8878

## N-Channel Power Trench® MOSFET

30V, 16.5A, 14mΩ

### Features

- Max  $r_{DS(on)}$  = 14mΩ at  $V_{GS}$  = 10V,  $I_D$  = 9.6A
- Max  $r_{DS(on)}$  = 17mΩ at  $V_{GS}$  = 4.5V,  $I_D$  = 8.7A
- Low Profile - 0.8 mm max in MLP 3.3X3.3
- RoHS Compliant

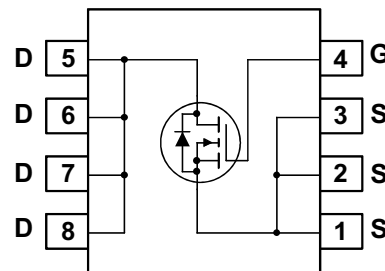
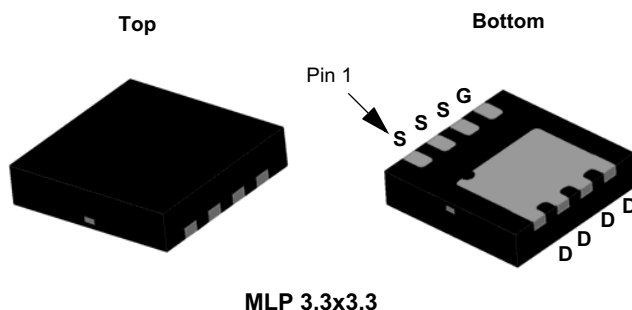


### General Description

This N-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced Power Trench process. It has been optimized for power management applications.

### Application

- DC - DC Conversion



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	16.5	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	38	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	9.6	
	-Pulsed	60	
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	31	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.1	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8878	FDMC8878	MLP 3.3X3.3	13 "	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		20		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$ , $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$			1 100	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	1	1.7	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-5.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 9.6\text{A}$		9.6	14.0	m $\Omega$
		$V_{GS} = 4.5\text{V}$ , $I_D = 8.7\text{A}$		12.1	17.0	
		$V_{GS} = 10\text{V}$ , $I_D = 9.6\text{A}$ , $T_J = 125^\circ\text{C}$		13.5	20.0	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{V}$ , $I_D = 9.6\text{A}$		35		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$		1000	1230	pF
$C_{oss}$	Output Capacitance			183	255	pF
$C_{rss}$	Reverse Transfer Capacitance			118	180	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		1.1		$\Omega$

**Switching Characteristics**

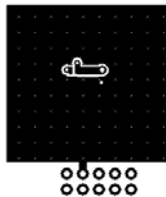
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}$ , $I_D = 9.6\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GEN} = 6\Omega$		8	16	ns
$t_r$	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			20	36	ns
$t_f$	Fall Time			3	10	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{V}$ , $V_{DD} = 15\text{V}$ , $I_D = 9.6\text{A}$		18	26	nC
$Q_{gs}$	Gate to Source Gate Charge			2.8		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			3.9		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = 9.6\text{A}$ (Note 2)		0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 9.6\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$		23	35	ns
$Q_{rr}$	Reverse Recovery Charge			14	21	nC

**Notes:**

1:  $R_{\theta JA}$  is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a.  $60^\circ\text{C}/\text{W}$  when mounted on  
a 1 in<sup>2</sup> pad of 2 oz copper



b.  $135^\circ\text{C}/\text{W}$  when mounted on a  
minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty cycle < 2.0%.

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

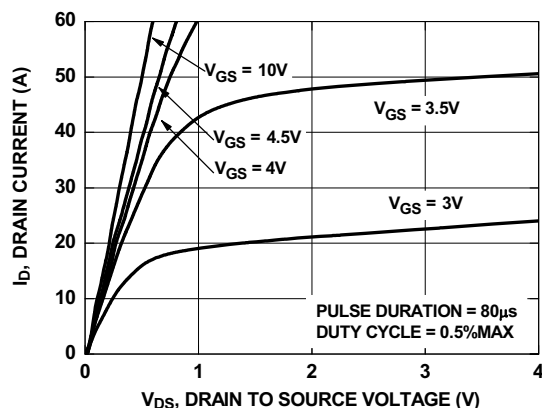


Figure 1. On-Region Characteristics

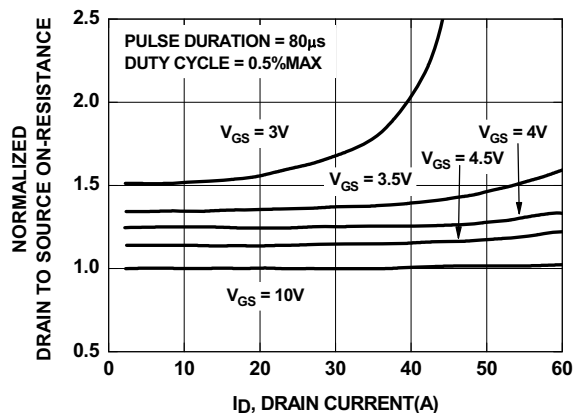


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

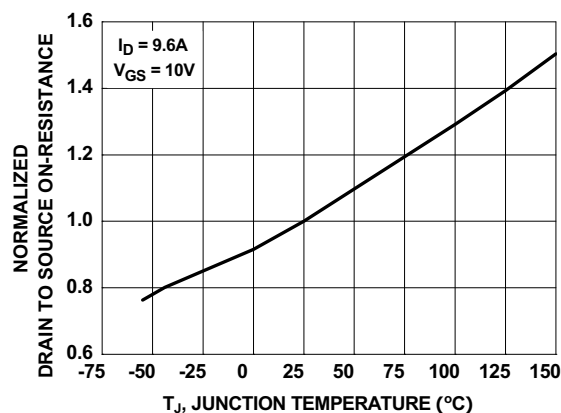


Figure 3. Normalized On-Resistance vs Junction Temperature

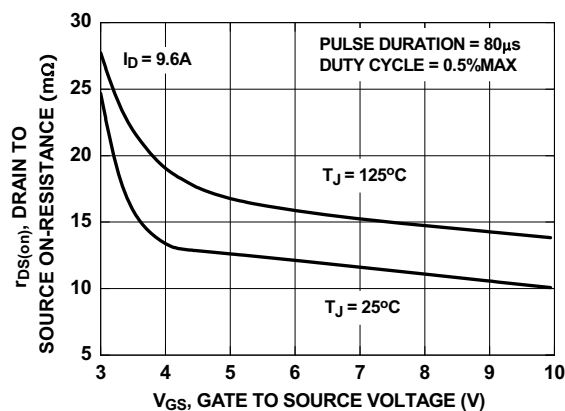


Figure 4. On-Resistance vs Gate to Source Voltage

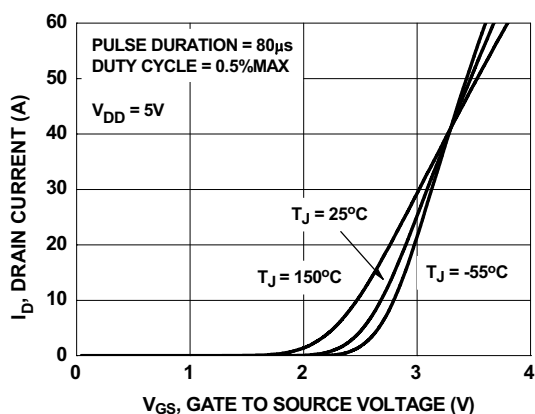


Figure 5. Transfer Characteristics

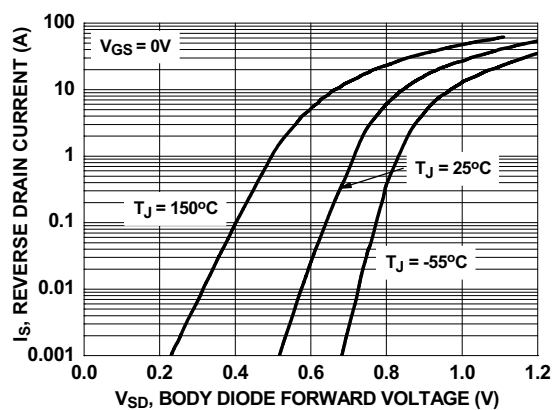


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

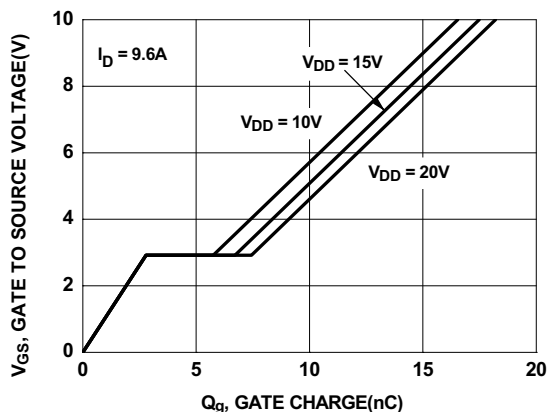


Figure 7. Gate Charge Characteristics

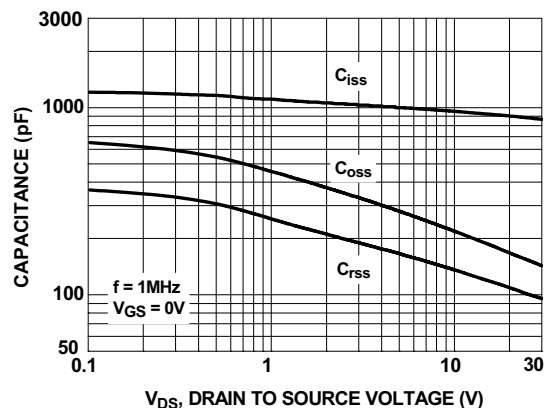


Figure 8. Capacitance vs Drain to Source Voltage

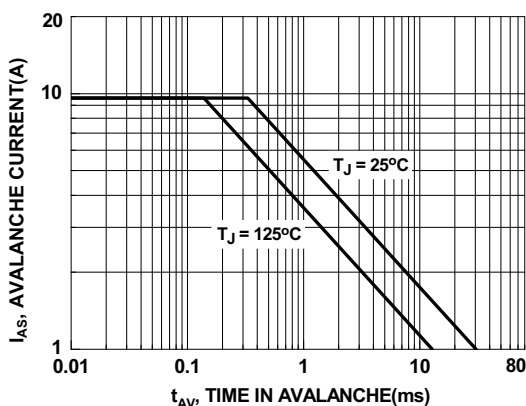


Figure 9. Unclamped Inductive Switching Capability

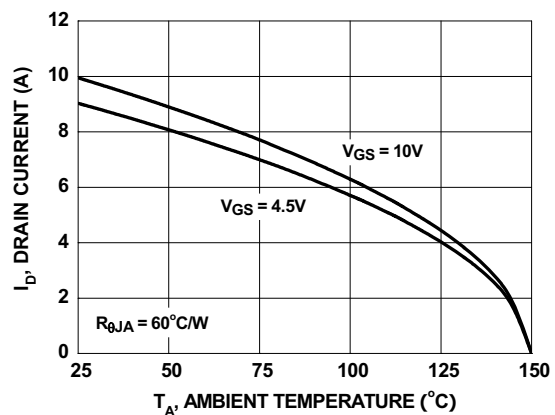


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

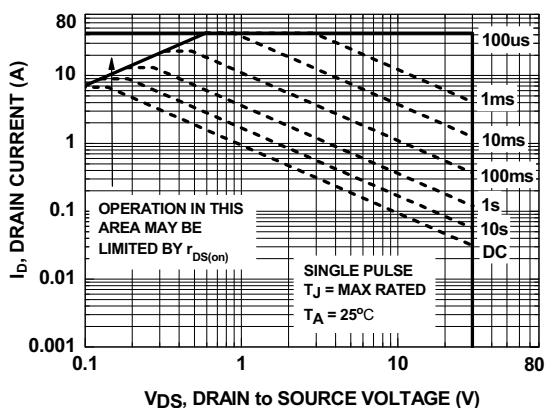


Figure 11. Forward Bias Safe Operating Area

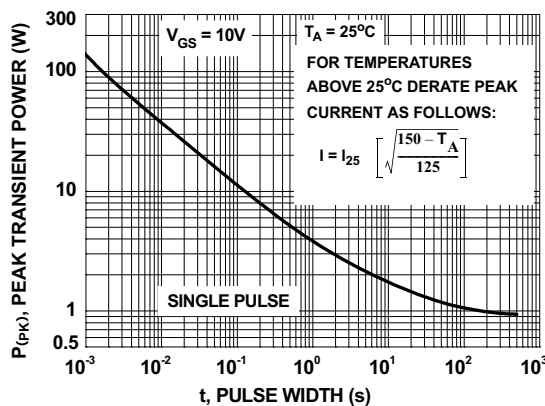
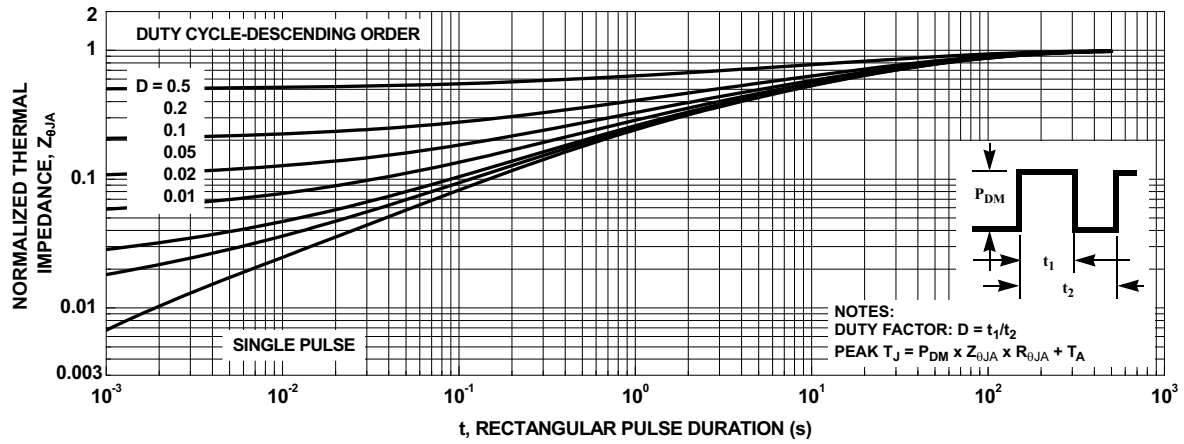
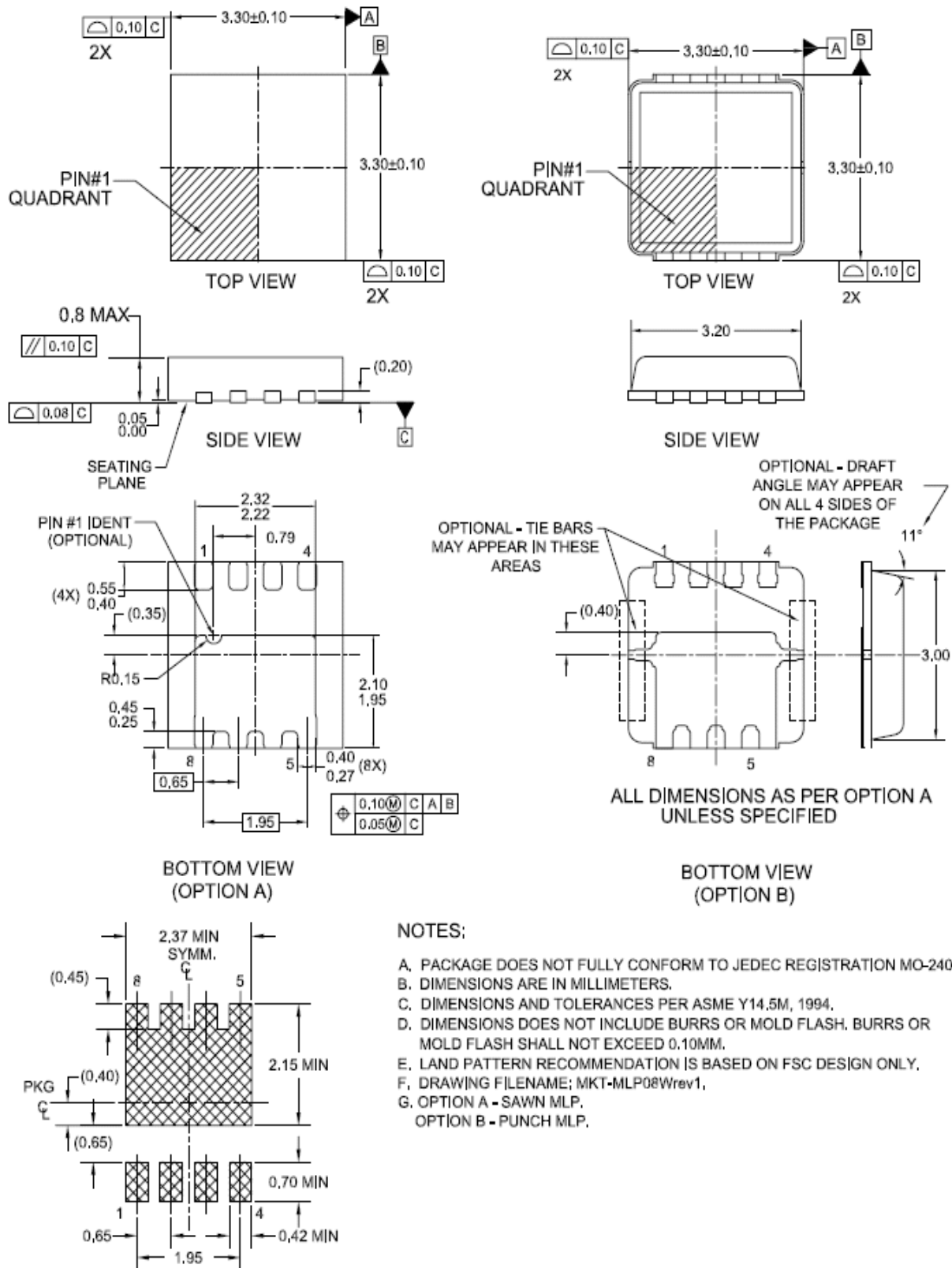


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



## Dimensional Outline and Pad Layout







### NOTES:

- PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
- DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS DOES NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
- LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY.
- DRAWING FILENAME: MKT-MLP08Wrev1.
- OPTION A - SAWN MLP.  
OPTION B - PUNCH MLP.



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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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